

09/920911

67,200-506  
000-0804

# ABSTRACT OF THE DISCLOSURE

Within a sequential and repetitive thermal oxidation and stripping method for forming a plurality of gate dielectric layers having a maximum numbered plurality of thicknesses upon a semiconductor substrate, there is provided a compensating thermal annealing when forming less than the maximum numbered plurality of thicknesses of the plurality of gate dielectric layers upon the semiconductor substrate. By employing the compensating thermal annealing, the semiconductor substrate is more readily manufacturable in conjunction with related microelectronic fabrications.

5

092091-0804